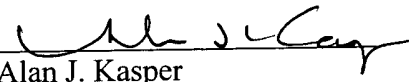


PRELIMINARY AMENDMENT  
Attorney Docket No.: Q68148

REMARKS

Accordingly, early and favorable consideration of the presently pending claims is respectfully requested.

Respectfully submitted,

  
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APPENDIX

VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

The claims are amended as follows:

6. A single crystal SiC, wherein:  
the single crystal SiC is obtained by a method claimed in ~~any one of claims 1 through 5~~,  
and  
the planar defect density of a topmost surface falls within a range not higher than  $10^3/\text{cm}^2$ .
7. A single crystal SiC, comprising:  
single crystal SiC obtained by a method claimed in ~~any one of claims 1 through 5~~, and  
another SiC deposited on the single crystal SiC by the vapor phase growth method or the  
liquid phase growth method.
10. A SiC composite material, comprising:  
single crystal SiC produced by a method claimed in ~~any one of claims 1 through 5~~, and  
diamond or GaN formed on the single crystal SiC.

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